



PARA LIGHT ELECTRONICS CO., LTD.



T +886-2-2225-3733

F +886-2-2225-4800



para@para.com.tw



11F, No. 8, Jiankang Rd., Zhonghe Dist., New Taipei City 23586, Taiwan



www.para.com.tw

PARA
ight
SINCE 1987



LED

Infrared LED & Optical Switch

- IP-Camara • Face Recognition • CCTV
- Vein Stria Recognition • IP-Camera

2021 Component Catalog



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Taiwan HQ

- 11F, No. 8, Jiankang Rd., Zhonghe Dist. New Taipei City, 23586 Taiwan
- +886-2-2225-3733 +886-2-2225-4800
- para@para.com.tw
- www.paralighttaiwan.com



Lianyungan Plant

- No.8, Wei Hai Rd., Guannan Economics Development Zone, Lianyungang City, Jiangsu Province, 222500, China
- +86-518-8369-2888
- +86-518-8369-2899
- para@para.com.tw



Nanjing Plant

- No.1, Tangquan W. Rd., Tangshan Ave., Jianning Dist. Nanjing City, Jiansu Province, 211131 China
- +86-25-8410-7685
- +86-25-8410-7684



USA Office

- 515 Spanish Lane, Suite # A&B, Walnut, CA 91789, USA
- +1 (877) 377-PARA / +1 (909) 468-4866
- sales@paralightusa.com
- www.paralightusa.com

Company Profile

Chairman : Mr. David Ma
 Established in 1987
 Capital : USD 37million
 No. of Employee : 1028

Founded in 1987, PARA LIGHT is now a global innovator and leader in visible and invisible LED fields. With two manufacturing plants certified with ISO 14001, ISO 9001, TS16969, and also complies with REACH and RoHS.

We offer advanced and beyond expectation R&D services based on the strongest lineup ever of 1,028 employees located in different countries and cities that includes more than 70 professional engineers, and 80 Quality Assurance squad.

About the product category, from the elementary LED component to further appli-
 ance such as UV sensor, LED back light, integrated light mouldule, commercial light-
 ing, automotive lighting and any lighting solution, PARA LIGHT keeps growing and
 expanding the products diversity in response to the global industry or market trend.

Quality Certification



IATF16949



ISO9001



ISO14001



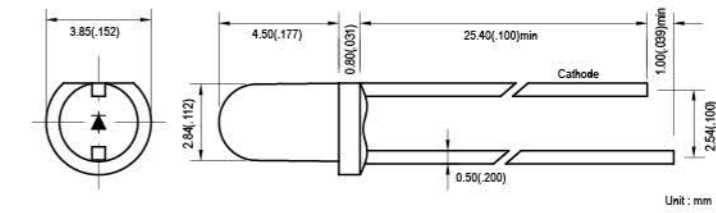


Emitter-Through hole Series



Application

- Remote Controller
- IP-Camara
- CCTV



L-31XXIR4X

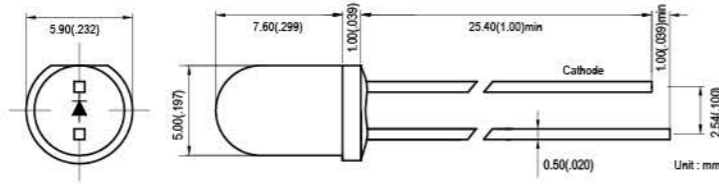
3 mm 850 nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_F (V)	Forward Current I_F (mA)
			Min.	Typ.		
L-314EIR4C	850 nm	20	20	70	1.4@ $I_F=20$ mA 1.6@ $I_F=100$ mA	20
L-316EIR4C	850 nm	30	8	15	1.4@ $I_F=20$ mA 1.6@ $I_F=100$ mA	20
L-318EIR4C	850 nm	40	20	70	1.4@ $I_F=20$ mA 1.6@ $I_F=100$ mA	20
L-319EIR4C	850 nm	20	10	20	1.4@ $I_F=20$ mA 1.6@ $I_F=100$ mA	20
L-31AEIR4C	850 nm	50	4	10	1.4@ $I_F=20$ mA 1.6@ $I_F=100$ mA	20

L-31XXIR1X

3 mm 940 nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_F (V)	Forward Current I_F (mA)
			Min.	Typ.		
L-314EIR1C	940 nm	20	7	12	1.2@ $I_F=20$ mA 1.4@ $I_F=100$ mA	20
L-316EIR1C	940 nm	30	6	15	1.2@ $I_F=20$ mA 1.4@ $I_F=100$ mA	20
L-318EIR1C	940 nm	40	6	18	1.2@ $I_F=20$ mA 1.4@ $I_F=100$ mA	20
L-314EIR1C	940 nm	20	2	6	1.2@ $I_F=20$ mA 1.4@ $I_F=100$ mA	20
L-316EIR1C	940 nm	30	6	15	1.2@ $I_F=20$ mA 1.4@ $I_F=100$ mA	20
L-318EIR1C	940 nm	40	4	8	1.2@ $I_F=20$ mA 1.4@ $I_F=100$ mA	20



L-51XXIR1X

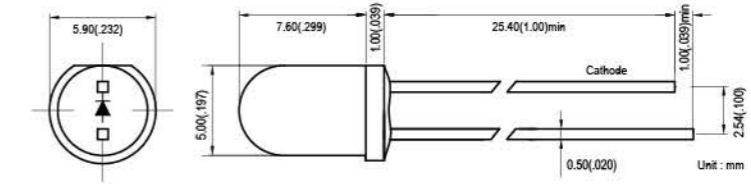
5 mm 940 nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-514EIR1C	940 nm	20	17	28	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-516EIR1C	940 nm	30	2	22	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-518EIR1C	940 nm	40	6	12	1.3@ $I_f=20$ mA 1.5@ $I_f=100$ mA	20
L-51CEIR1C	940 nm	60	4	8	1.3@ $I_f=20$ mA 1.5@ $I_f=100$ mA	20
L-514EIR1BC	940 nm	20	15	30	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-516EIR1BC	940 nm	30	12	20	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-518EIR1BC	940 nm	40	8	18	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20
L-51AEIR1BC	940 nm	50	2	5	1.2@ $I_f=20$ mA 1.4@ $I_f=100$ mA	20

L-51XXIR3X

5 mm 865 nm

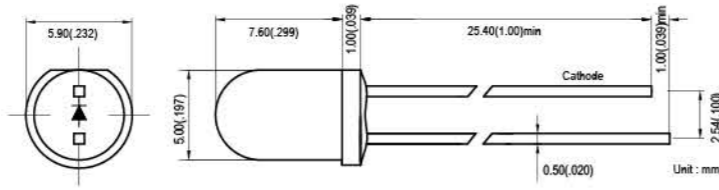
Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-514EIR3C	865 nm	20	30	50	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR3C	865 nm	30	12	30	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR3C	865 nm	40	10	22	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR3C	865 nm	50	10	20	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-514EIR3BC	865 nm	20	25	45	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR3BC	865 nm	30	12	25	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR3BC	865 nm	40	10	20	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR3BC	865 nm	50	10	18	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20



L-51XXIR4XX

5 mm 850 nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-514GIR4C	850 nm	20	60	175	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-516GIR4C	850 nm	30	30	80	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-518GIR4C	850 nm	40	60	85	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-51AGIR4C	850 nm	50	28	40	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-514GIR4BC	850 nm	20	127	170	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-516GIR4BC	850 nm	30	112	160	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100
L-518GIR4BC	850 nm	40	55	85	1.4@ $I_f=20$ mA 1.5@ $I_f=100$ mA	100



L-51XXIR2X

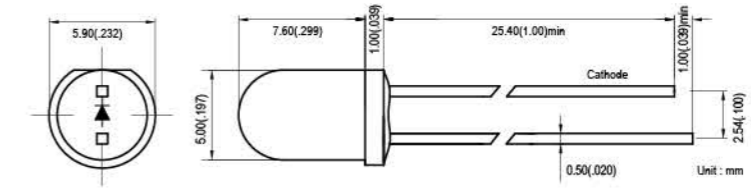
5 mm 880 nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-514EIR2C	880 nm	20	17	28	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR2C	880 nm	30	2	7	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR2C	880 nm	40	20	50	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR2C	880 nm	50	4	10	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-514EIR2BC	880 nm	20	15	30	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR2BC	880 nm	30	15	30	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR2BC	880 nm	40	8	21	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR2BC	880 nm	50	4	8	1.3@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20

L-51XXIR4X

5 mm 850 nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L-514EIR2C	850 nm	20	25	45	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR2C	850 nm	30	14	45	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR2C	850 nm	40	10	20	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR2C	850 nm	50	8	25	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-514EIR2BC	850 nm	20	8	20	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-516EIR2BC	850 nm	30	20	70	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-518EIR2BC	850 nm	40	12	40	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR2BC	850 nm	50	12	35	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20
L-51AEIR2BC	850 nm	50	10	25	1.4@ $I_f=20$ mA 1.6@ $I_f=100$ mA	20



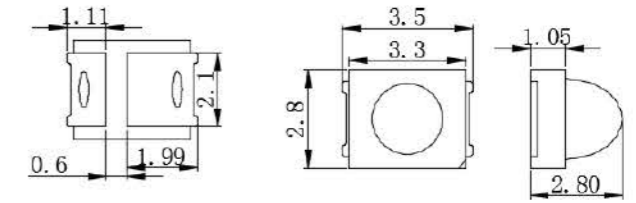
L-5PGEIRXX

5 mm 850 nm / 940 nm

Part No.	Wavelength λ_d (nm)	Viewing Angle (deg.)	Radiation Intensity I_e (mW/sr)		Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
			Min.	Typ.		
L5PGEIR4C	850 nm	80	4	8	1.2	20
L5PGEIR1C	940 nm	80	2	4	1.2	20



Emitter-PLCC Series



LT2835

2.8x3.5x2.42 mm

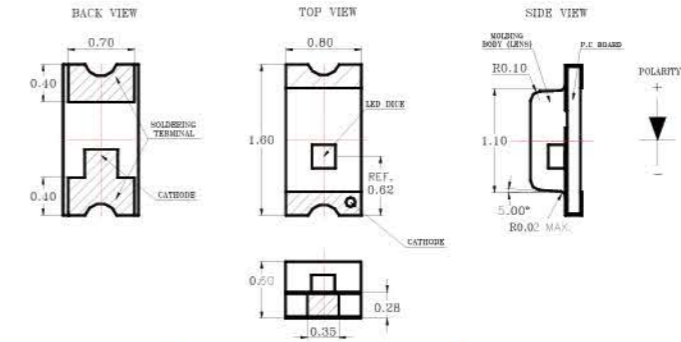
Part No.	Wavelength λ_d (nm)	Lens Type	Viewing Angle (deg.)	Typ. Radiation Intensity I_e (mW/sr)	Typ. Forward Voltage V_f (V)	Forward Current I_f (mA)
L-T2835IR4CT-30	850 nm	Water Clear	30	80~140	1.2~1.7	150
L-T2835IR4CT-60	850 nm	Water Clear	60	80~140	1.2~1.7	150
L-T2835IR4CT-90	850 nm	Water Clear	90	60~100	1.2~1.7	150



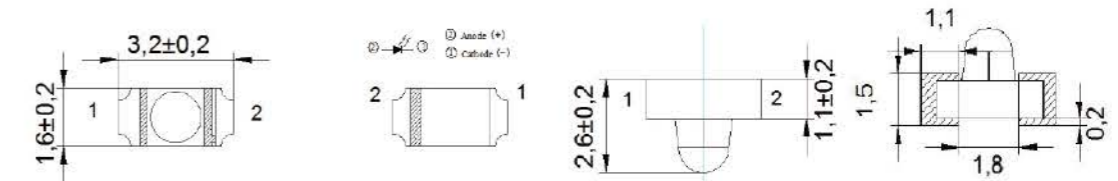
Application

- IP-Camera
- CCTV
- Drowsy Driver Detection
- Iris Recognition
- Face Recognition
- AR/ VR / Gesture Recognition / VCSEL 3D Sensing (TOF)
- Vein Stria Recognition

Emitter-SMD Series



Part No.	Package	Reverse Light Current (IL)	Wavelength(nm)	Viewing Angle(°)
LC191IR1CT	SMD	10	940 nm	130



Part No.	Package	Reverse Light Current (IL)	Wavelength(nm)	Viewing Angle(°)
LS156AIR1C-HD	SMD	10	940 nm	30



Application

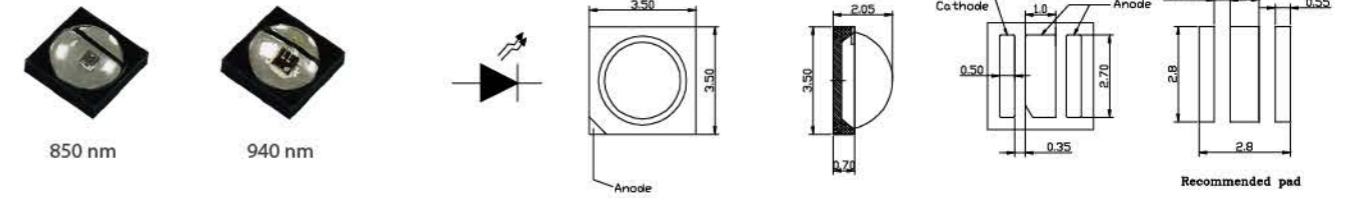
- IP-Camera
- CCTV
- Drowsy Driver Detection
- Iris Recognition
- Face Recognition
- AR/ VR / Gesture Recognition / VCSEL 3D Sensing (TOF)
- Vein Stria Recognition

Emitter- High power Series



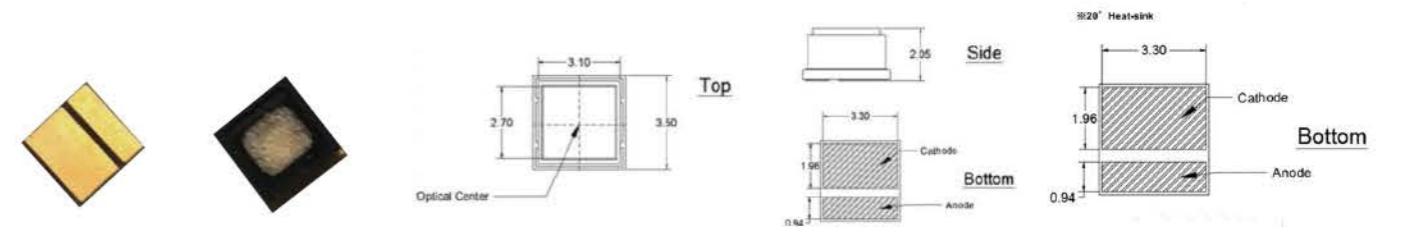
Application

- Drowsy Driver Detection
- Iris Recognition
- Face Recognition
- AR / VR / Gesture Recognition / VCSEL 3D Sensing (TOF)
- Vein Stria Recognition



L-T3535

Part No.	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
LT3535IR4CT-N-P-E-B	350 mA	250 mW	850 nm	120
LT3535IR4CT-N-Y-E-B	350 mA	240 mW	850 nm	150
LT3535IR4CT-R-P-E-B	350 mA	195 mW	850 nm	120
LT3535IR4CT-R-Y-E-B	1000 mA	145 mW	850 nm	150
LT3535IR4CT-U-P-E-B	1000 mA	175 mW	850 nm	120
LT3535IR4CT-U-Y-E-B	1000 mA	165 mW	850 nm	150
LT3535IR1CT-N-Y-E-B	350 mA	40 mW	940 nm	150



Part No.	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
L-T3535IR1CT-55-72-1W-ZGY	1.25 mA	1000 mW	940 nm	55 / 72
L-T3535IR1CT-55-72-2W-ZGY	2.5 mA	2000 mW	940 nm	55 / 72



Vein Stria Recognition

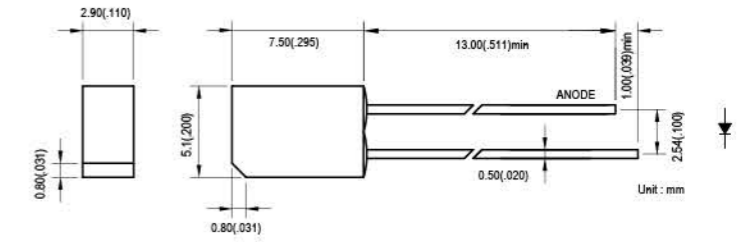
Drowsy Driver Detection



Photodiode

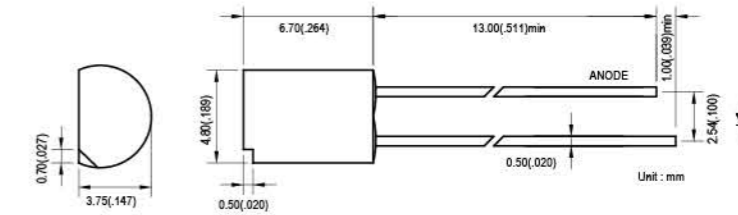
Application

- Smoking Detector
- Detecting Object



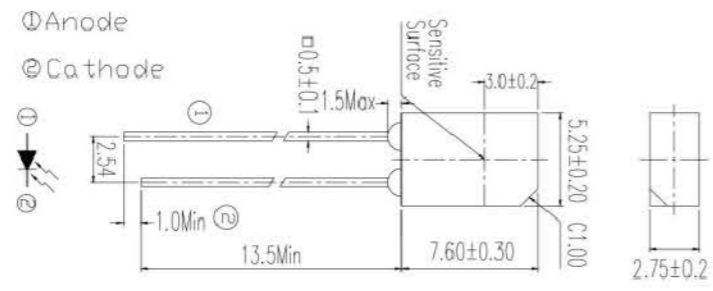
L-SB1R9PD1X

Part No.	Max. Reverse Dark Current I_D (nA) @ $V_R=10V$; $E_e=0 \text{ mW/cm}^2$	Min. Reverse Voltage $V(BR)R$ (V) @ $I_R=100\mu A$; $E_e=0 \text{ mW/cm}^2$	Typ. Open Circuit Voltage V_{OC} (V) @ $E_e=5 \text{ mW/cm}^2$	Typ. Light Current I_L (μA) @ $V_R=5V$; $E_e=5 \text{ mW/cm}^2$	Total Capacitance C_T (PF) @ $f=1 \text{ mhz}$; $V_R=5V$; $E_e=0 \text{ mW/cm}^2$	Spectral Sensitivity Wavelength λ_p (nm)		
						Min.	Typ.	Max.
L-SB1R9PD1C	30	33	390	40	18	400		1050
L-SB1R9PD1D1	30	33	390	40	18	900	940	
L-SB1R9PD1D2	30	33	390	40	18	800	870	



L-SC1R9PD1X

Part No.	Max. Reverse Dark Current I_D (nA) @ $V_R=10V$; $E_e=0 \text{ mW/cm}^2$	Min. Reverse Voltage $V(BR)R$ (V) @ $I_R=100\mu A$; $E_e=0 \text{ mW/cm}^2$	Typ. Open Circuit Voltage V_{OC} (V) @ $E_e=5 \text{ mW/cm}^2$	Typ. Light Current I_L (μA) @ $V_R=5V$; $E_e=5 \text{ mW/cm}^2$	Total Capacitance C_T (PF) @ $f=1 \text{ mhz}$; $V_R=5V$; $E_e=0 \text{ mW/cm}^2$	Spectral Sensitivity Wavelength λ_p (nm)		
						Min.	Typ.	Max.
L-SC1R9PD1C	30	33	390	40	18	400		1050
L-SC1R9PD1D1	30	33	390	40	18	900	940	
L-SC1R9PD1D2	30	33	390	40	18	800	870	



Part No.	Package	Reverse Light Current (IL)	Wavelength(nm)	Viewing Angle(°)
L-SB1R12PD1D1-ZGY	DIP	25	840 nm ~ 1100 nm	120

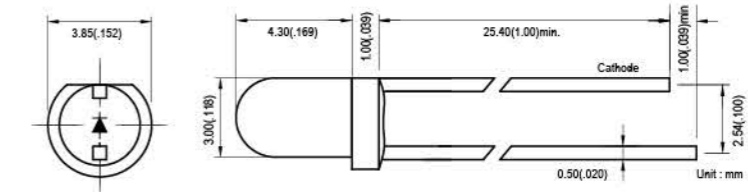


Phototransistor



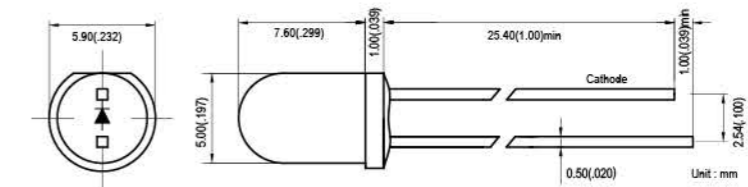
Application

- Photo-Switch
- Detecting Object
- Decoder



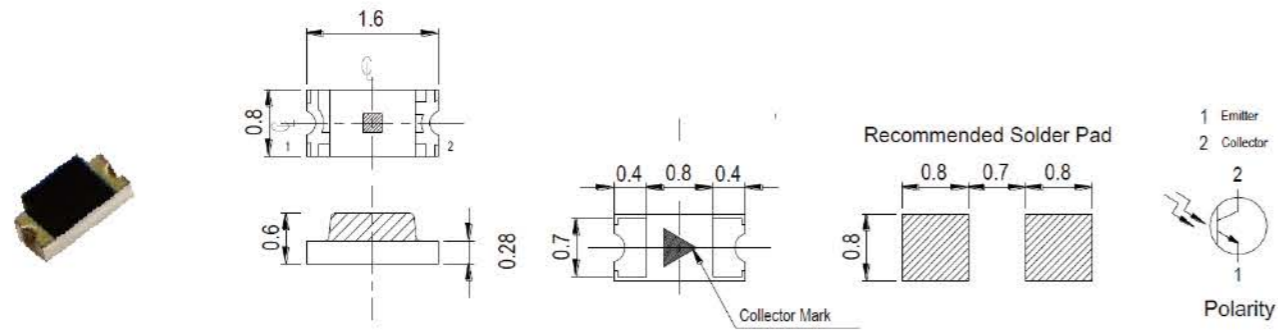
L-31ROPT1X

Part No.	Min. Collector-Emitter Breakdown Voltage $BV_{CEO}(V)$ @ $I_C=100\mu A$; $E_e=0\text{ mW/cm}^2$	Min. Emitter-Collector Breakdown Voltage $BV_{ECO}(V)$ @ $I_C=100\mu A$; $E_e=0\text{ mW/cm}^2$	Max. Collector Dark Current $I_{CEO}(nA)$ @ $V_{CE}=10V$; $E_e=0\text{ mW/cm}^2$	Max. Collector-Emitter Saturation Voltage $V_{CE(S)}(V)$ @ $I_C=2mA$; $E_e=0.5\text{ mW/cm}^2$	Typ. On State Collector Current $I_C(mA)$ @ $V_{CE}=5V$; $E_e=0.1\text{ mW/cm}^2$	Spectral Sensitivity Wavelength $\lambda_p(nm)$		
						Min.	Typ.	Max.
L-31ROPT1C	30	5	100	0.4	4	400		1050
L-31ROPT1D1	30	5	100	0.4	1.2	900	940	
L-31ROPT1D2	30	5	100	0.4	2	800	870	

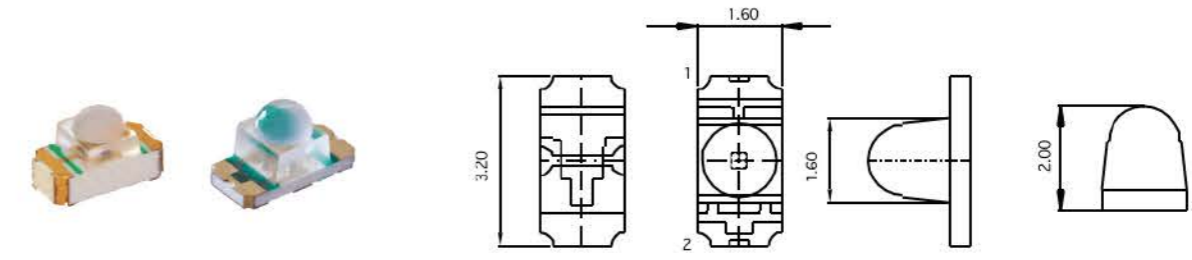


L-51ROPT1X

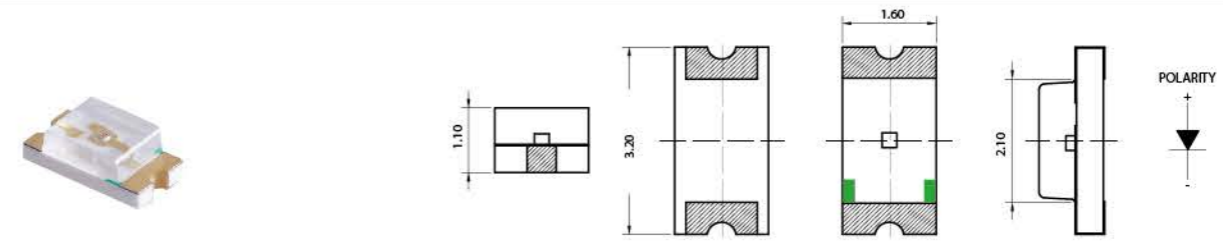
Part No.	Min. Collector-Emitter Breakdown Voltage $BV_{CEO}(V)$ @ $I_C=100\mu A$; $E_e=0\text{ mW/cm}^2$	Min. Emitter-Collector Breakdown Voltage $BV_{ECO}(V)$ @ $I_C=100\mu A$; $E_e=0\text{ mW/cm}^2$	Max. Collector Dark Current $I_{CEO}(nA)$ @ $V_{CE}=10V$; $E_e=0\text{ mW/cm}^2$	Max. Collector-Emitter Saturation Voltage $V_{CE(S)}(V)$ @ $I_C=2mA$; $E_e=0.5\text{ mW/cm}^2$	Typ. On State Collector Current $I_C(mA)$ @ $V_{CE}=5V$; $E_e=0.1\text{ mW/cm}^2$	Spectral Sensitivity Wavelength $\lambda_p(nm)$		
						Min.	Typ.	Max.
L-51ROPT1C	30	5	100	0.4	2	400		1050
L-51ROPT1D1	30	5	100	0.4	1.2	900	940	
L-51ROPT1D2	30	5	100	0.4	1.2	800	870	



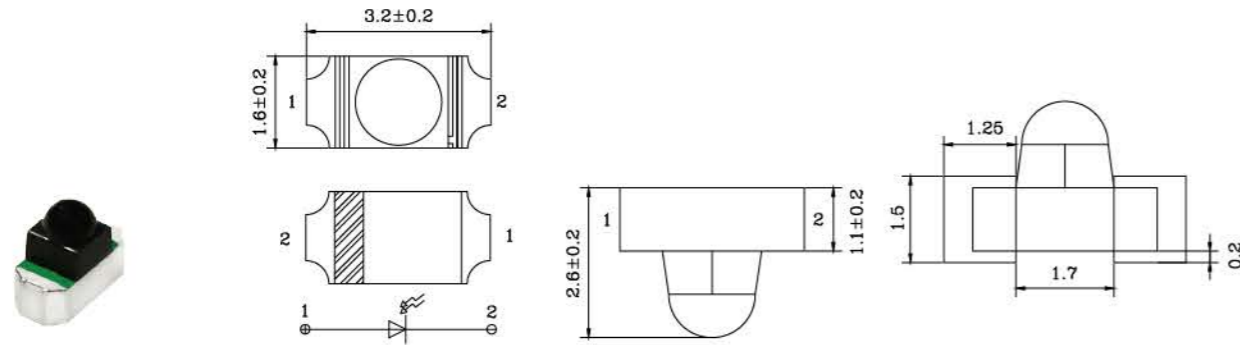
Part No.	Min. Collector-Emitter Breakdown Voltage $BV_{CEO}(V)$ @ $I_C=100\mu A$; $E_e=0 \text{ mW/cm}^2$	Min. Emitter-Collector Breakdown Voltage $BV_{ECO}(V)$ @ $I_E=100\mu A$; $E_e=0 \text{ mW/cm}^2$	Max. Collector Dark Current $I_{CEO}(nA)$ @ $V_{CE}=20V$; $E_e=0 \text{ mW/cm}^2$	Max. Collector-Emitter Saturation Voltage $V_{CE(S)}(V)$ @ $I_C=2mA$; $E_e=1 \text{ mW/cm}^2$	Typ. On State Collector Current $I_C(mA)$ @ $V_{CE}=5V$; $E_e=1 \text{ mW/cm}^2$	Spectral Sensitivity Wavelength $\lambda_p(nm)$		
						Min.	Typ.	Max.
LC191PTBT-HD	30	5	100	0.4	1.14	940		



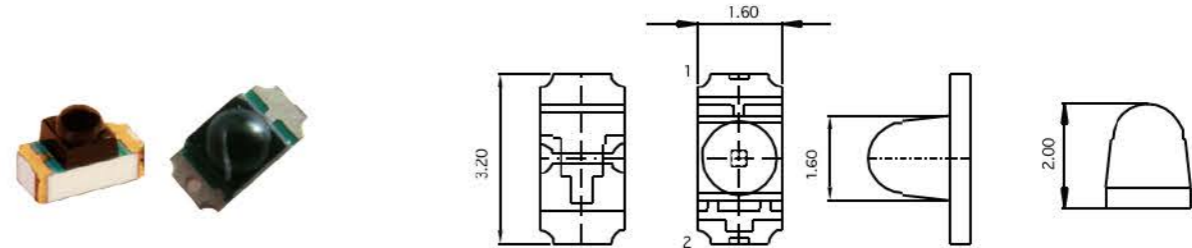
Part No.	Wavelength $\lambda_d(nm)$	Forward Current $I_F(mA)$	Radiant Intensity $I_e(mW/sr)$		Typ. Forward Voltage $V_F(V)$ 1.4@ $I_F=20mA$ 1.6@ $I_F=100mA$	Viewing Angle($^\circ$)
			Min.	Typ.		
LS153IR1CT	940 nm	20	6	9		30



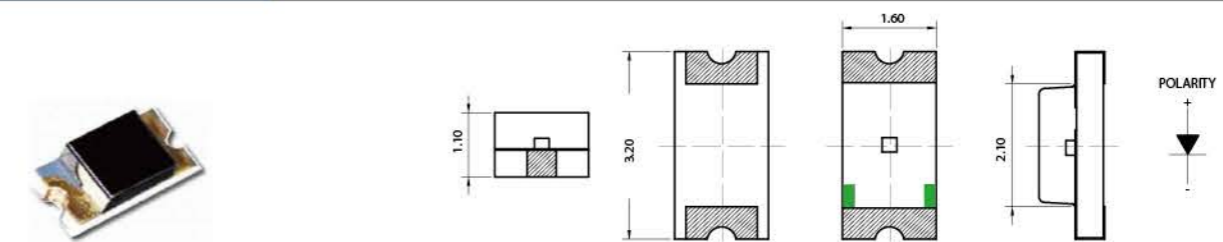
Part No.	Wavelength $\lambda_d(nm)$	Forward Current $I_F(mA)$	Radiant Intensity $I_e(mW/sr)$		Typ. Forward Voltage $V_F(V)$ 1.4@ $I_F=20mA$ 1.6@ $I_F=100mA$	Viewing Angle($^\circ$)
			Min.	Typ.		
LC150IR1CT	940 nm	20	0.45	1.2		130



Part No.	Min. Collector-Emitter Breakdown Voltage $BV_{CEO}(V)$ @ $I_C=100\mu A$; $E_e=0 \text{ mW/cm}^2$	Min. Emitter-Collector Breakdown Voltage $BV_{ECO}(V)$ @ $I_E=100\mu A$; $E_e=0 \text{ mW/cm}^2$	Max. Collector Dark Current $I_{CEO}(nA)$ @ $V_{CE}=10V$; $E_e=0 \text{ mW/cm}^2$	Max. Collector-Emitter Saturation Voltage $V_{CE(S)}(V)$ @ $I_C=2mA$; $E_e=1 \text{ mW/cm}^2$	Typ. On State Collector Current $I_C(mA)$ @ $V_{CE}=5V$; $E_e=1 \text{ mW/cm}^2$	Spectral Sensitivity Wavelength $\lambda_p(nm)$		
						Min.	Typ.	Max.
LS153PTDT-LENS-RB	30	5	30	0.4	1.0	940		



Part No.	Package	Light Current (mA)	Wavelength (nm)	Viewing Angle($^\circ$)
LS153PTDT	SMD	2.6	900 nm ~ 940 nm	30



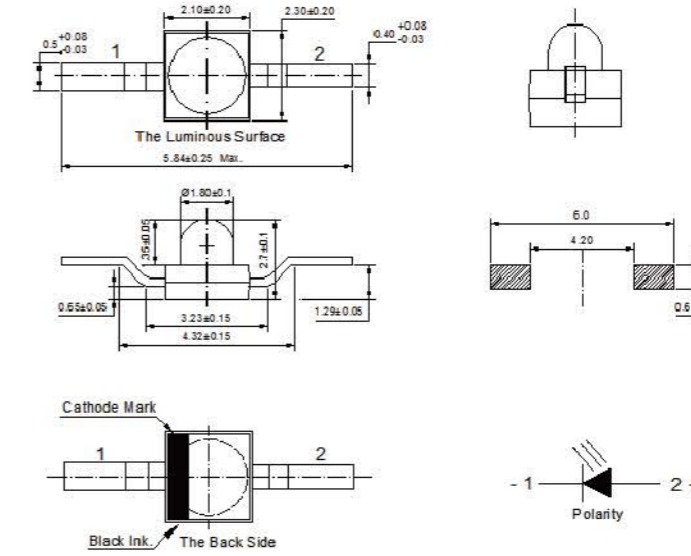
Part No.	Package	Light Current (mA)	Wavelength (nm)	Viewing Angle($^\circ$)
LC150PTDT	SMD	2	900 nm ~ 940 nm	130

Transmitter and Receiver

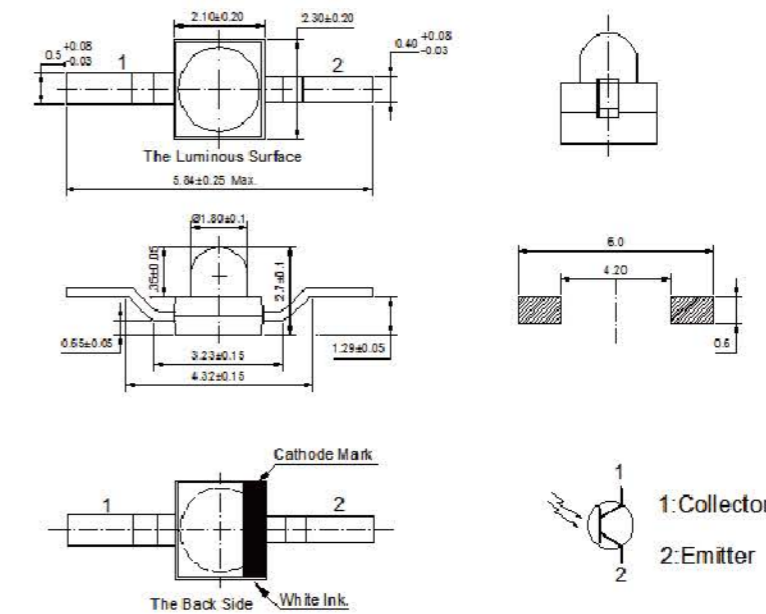


Application

- IP-Camera
- Photoelectric encoder



Part No.	Wavelength λ_d (nm)	Forward Current I_f (mA)	Radiant Intensity I_e (mW/sr)		Typ. Forward Voltage V_F (V)	Viewing Angle(°)
			Min.	Typ.		
L180IR1C-BKS-TR10	940 nm	20	3.0	5.0	1.4@ $I_f=20mA$ 1.6@ $I_f=100mA$	25

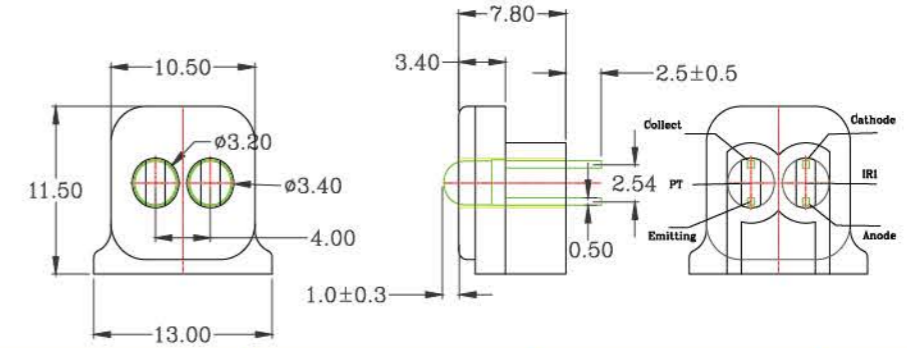


Part No.	Package	Light Current (mA)	Wavelength (nm)	Viewing Angle(°)
L180PT1DT-BKR-TR10	SMD	20	730 nm ~ 1100 nm	25

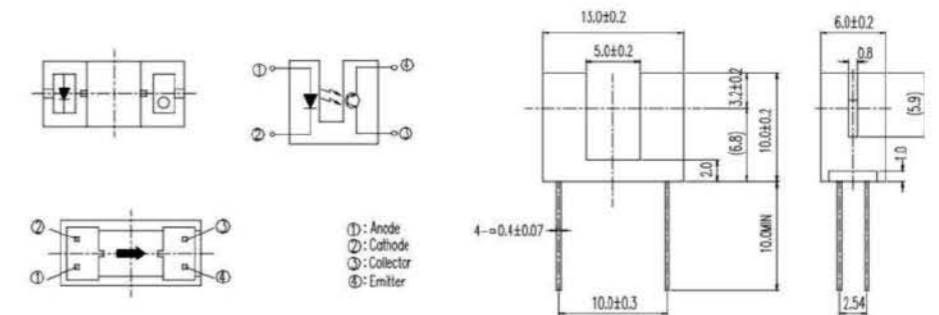


Application

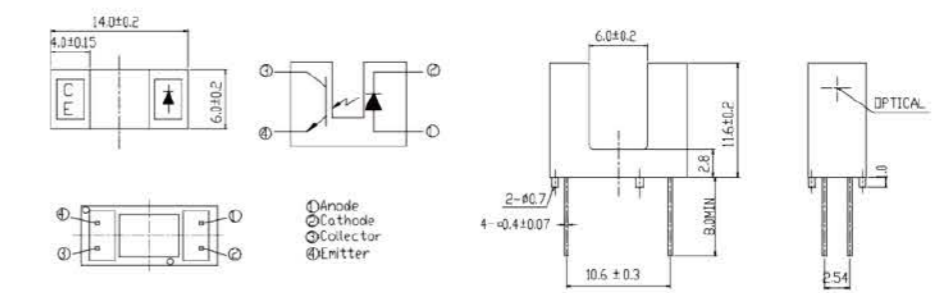
- Liquid Level Sensor
- Optical Sensor
- PM2.5 Sensor
- Avoidance Sensor
- Smoke Detector
- Servo Motor-Encoder
- Bit / Bubble Monitor Sensor



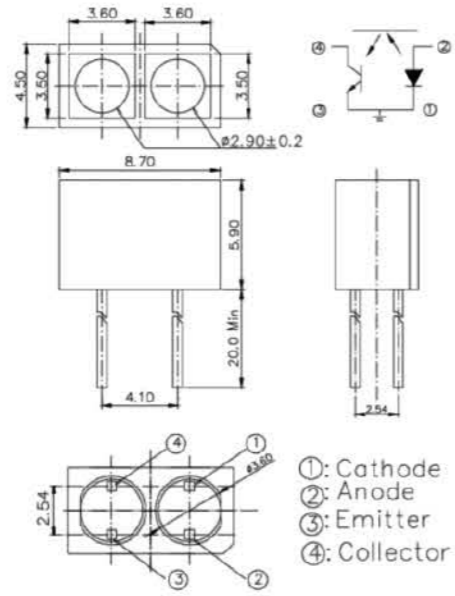
Part No.	Package	Input (Emitter)	Output (Detector)	Tr / Tf (μs)
ITRH001	DIP	45 mW	30 mA	25 / 25



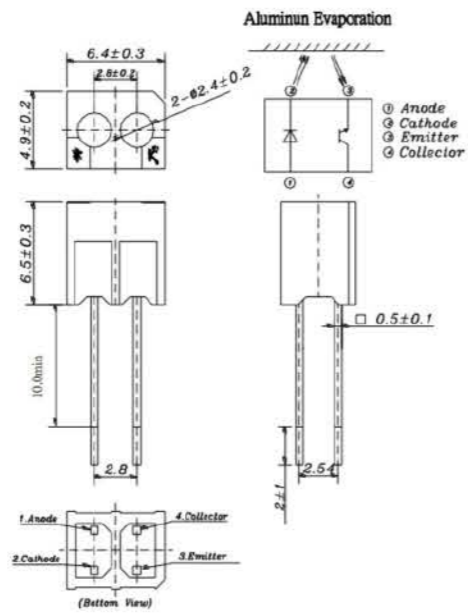
Part No.	Package	Input (Emitter)	Output (Detector)	Tr / Tf (μs)
ITR2005002	DIP	75 mW	75 mW	15 / 15



Part No.	Package	Input (Emitter)	Output (Detector)	Tr / Tf (μs)
ITR2012001	DIP	75 mW	75 mW	15 / 15



Part No.	Package	Input (Emitter)	Output (Detector)	Tr / Tf (μ s)
ITR2005003	DIP	75 mW	75 mW	15 / 15



Part No.	Package	Input (Emitter)	Output (Detector)	Tr / Tf (μ s)
ITR2012002	DIP	75 mW	75 mW	15 / 15

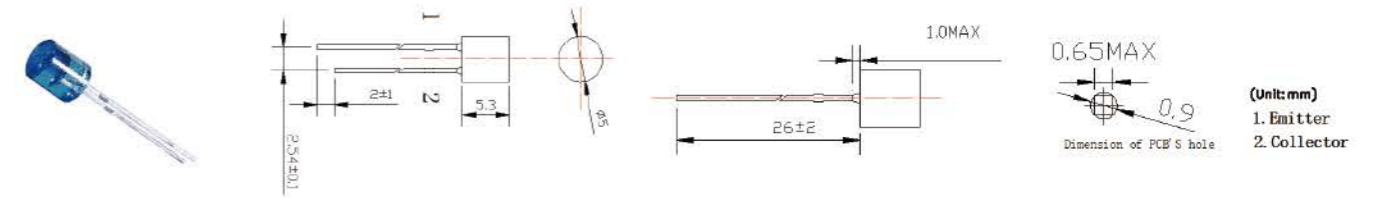


Optical sensor- Ambient light sensor

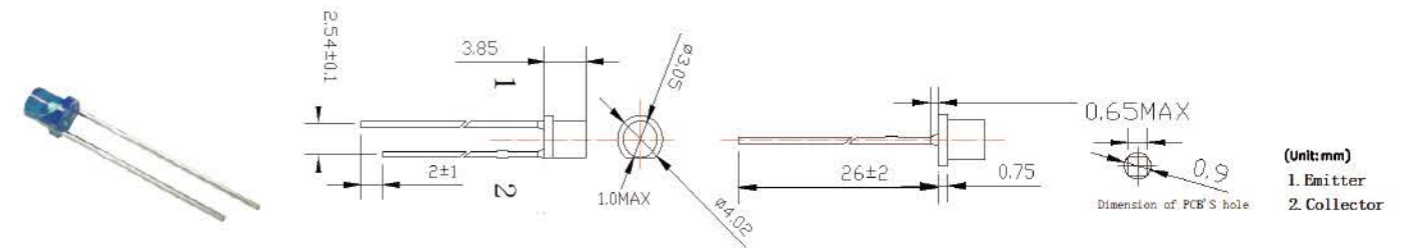


Application

- Detection of ALS to Control IR LED
- Automatic contrast for light change



Part No.	Package	On State Collector Current (Ev=30Lux)	Wavelength(nm)	Viewing Angle(°)
L5Q3IRT-JNJ	DIP	15	550 nm	120



Part No.	Package	Radiant Intensity(mW/sr)	Wavelength(nm)	Viewing Angle(°)
L334IRT-JNJ	DIP	15	550 nm	120

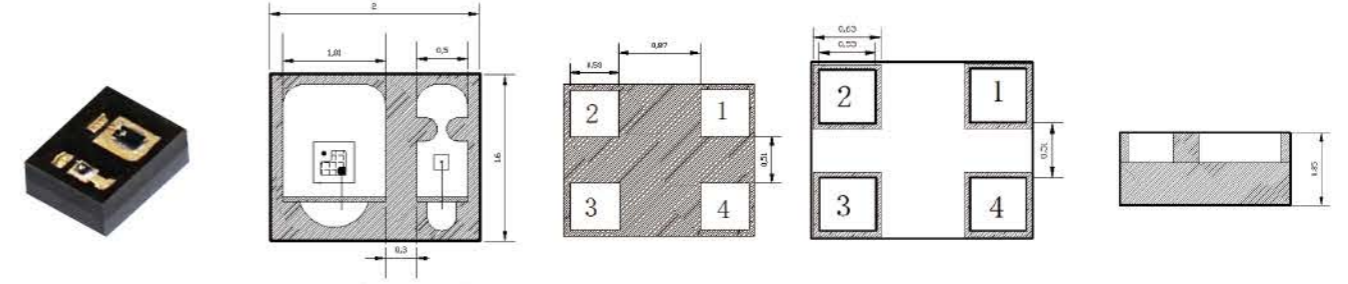


Optical sensor- TWS Proximity sensor

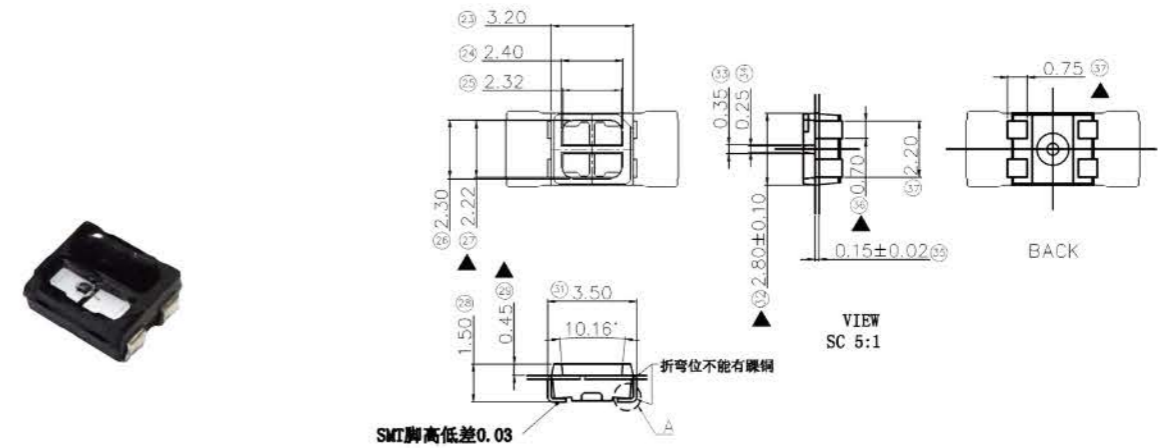


Application

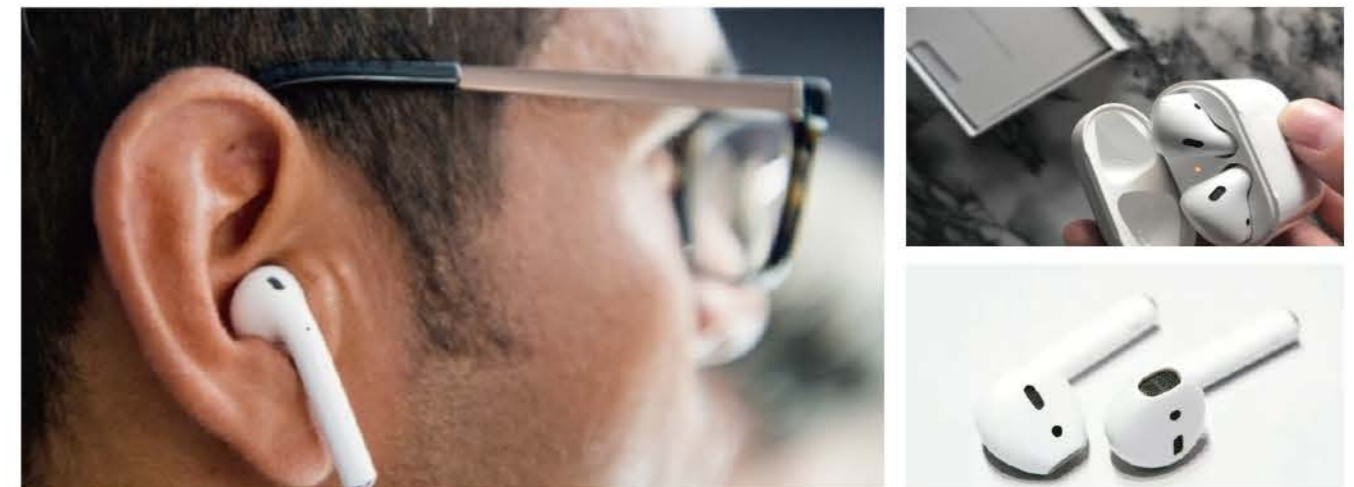
- TWS-Earphone
- Proximity Sensor



Part No.	Package	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
LT2016R1CT-JNJ	SMD	10 mA	12	940 nm	120



Part No.	Package	Input (Emitter)	Input (Emitter)	Tr / Tf (μs)
ITR8307	PLCC	75 mW	75 mW	20 / 20



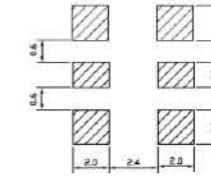
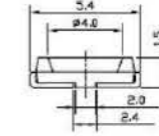
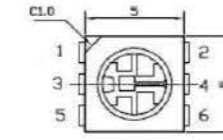


Optical sensor- Pulse sensor



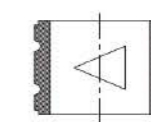
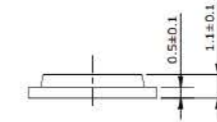
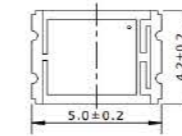
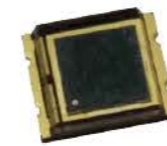
Application

- Food
- Skin Moisture
- Gas Measurement
- Blood Oxygen
- Pulse Sensor



1 → 2 1400nm
 3 → 4 1300nm
 5 → 6 1050nm
 Tolerance: ±0.1
 Unit : mm

Part No.	Package	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
LT69F3IN1CT-JNJ	PLCC	100 mA	33 / 34 / 25	1050nm / 1300nm / 1400nm	120



Part No.	Package	Reverse Light Current (IL)	Wavelength(nm)	Viewing Angle(°)
LC5042PDC-ZGY	SMD	25	400 nm ~ 1100 nm	120

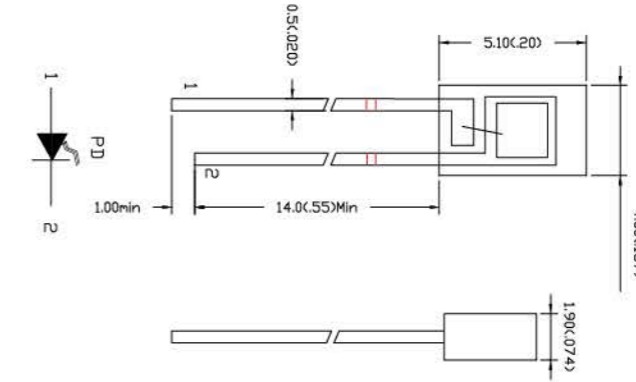


Optical sensor- Pulse oximeter sensor



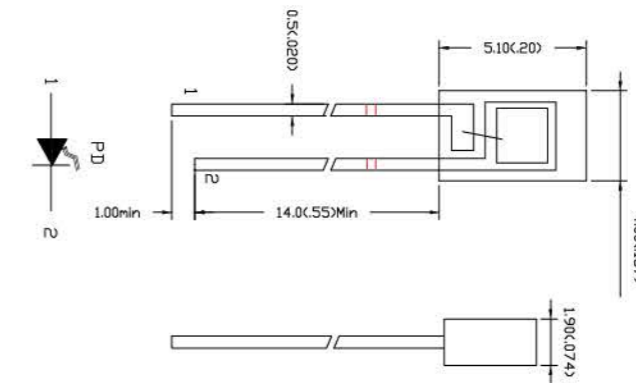
Application

- Pulse oximeter



LSC1R9PD1C

Lens Type	Reverse Breakdown BVR(V) E _e =0mW/cm ² IR=100μA	Total Capacitance CT(pF) E _e =0mW/cm ² VR=3V F=1MHZ	Max. Collector Dark Current I _{CEO} (nA) @V _{CE} =10V; E _e =0 mW/cm ²	Max. Collector-Emitter Saturation Voltage V _{CE(S)} (V) @I _C =2mA; E _e =5mW/cm ²	Typ. On State Collector Current I _C (mA) @V _{CE} =5V; E _e =1mW/cm ²	Spectral Sensitivity Wavelength λ _p (nm)		
						Min.	Typ.	Max.
Water Clear	170	7.3	5	0.35	18	400		1100



LSC2HIRC

Lens Type	Wavelength λ _d (nm)		Typ. Radiation Intensity I _e (mW/sr)		Typ. Forward Voltage V _f (V)		Forward Current I _F (mA)		Viewing Angle (deg.)
	R	IR	R	IR	R	IR	R	IR	
Water Clear	660 nm	905 nm	60	50	2.6	1.6	30	50	-

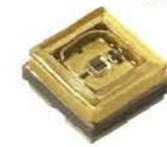


Application

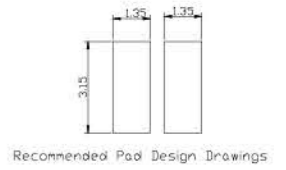
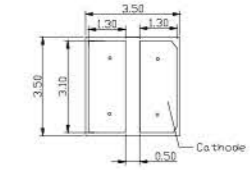
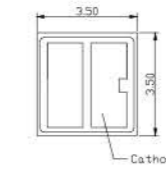
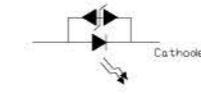
- Ultraviolet disinfection
- Phototherapy
- Bio- Analysis / Detection
- General use



NEW



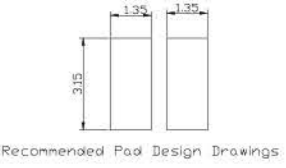
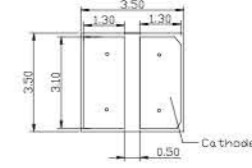
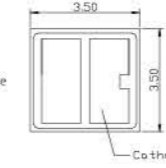
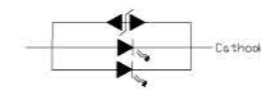
LT3535UVC-KPC



NEW



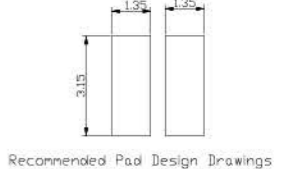
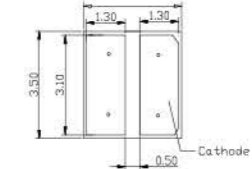
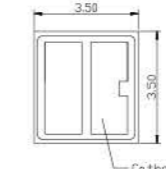
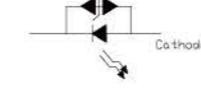
LT3535UVC-KPCA1



NEW



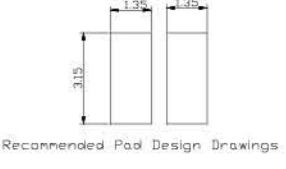
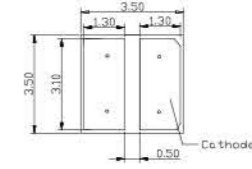
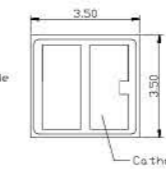
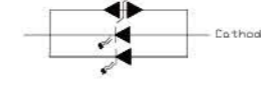
LT3535UVC-K1PC



NEW




LT3535UVC-K1PCA1


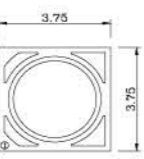
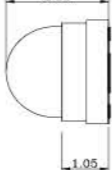
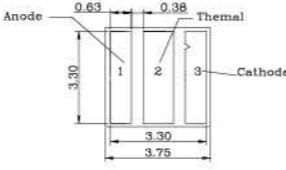
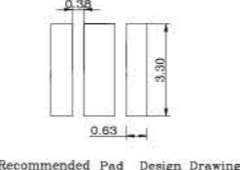


Part No.	Package	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
LT3535UVC-KPC	SMD	80 mA	9.2 mW	275 nm	120
LT3535UVC-KPCA1	SMD	150 mA	18.4 mW	275 nm	120
LT3535UVC-K1PC	SMD	40 mA	4 mW	275 nm	120
LT3535UVC-K1PCA1	SMD	80 mA	8 mW	275 nm	120


NEW




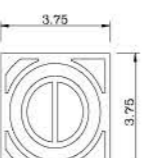
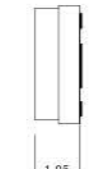
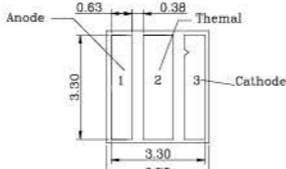
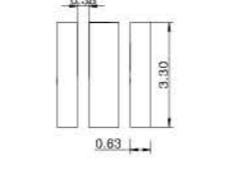
LT3535UVC-KCCM

NEW




LT3535UVC-KPCM


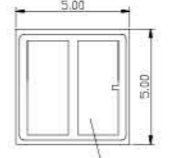
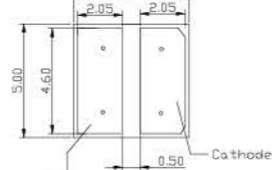

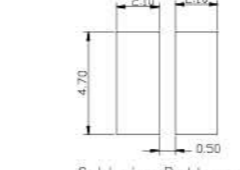






Part No.	Package	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
LT3535UVC-KCCM	SMD	100 mA	20 mW	275 nm	60
LT3535UVC-KPCM	SMD	100 mA	15 mW	275 nm	120


NEW




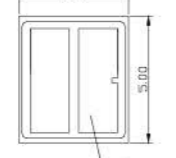
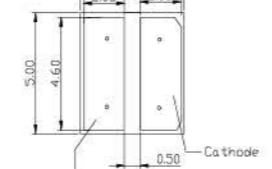
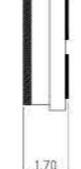
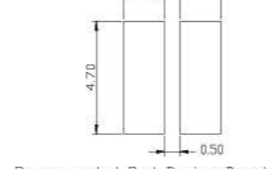
LT5050UVC-XPC


NEW



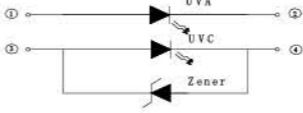
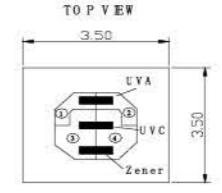
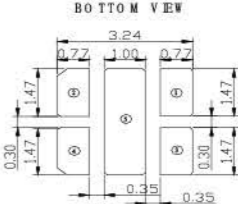

LT5050UVC-XPCA1

Part No.	Package	test condition (IF)	Radiant Intensity(mW)	Wavelength(nm)	Viewing Angle(°)
LT5050UVC-XPC	SMD	350 mA	28 mW	275 nm	120
LT5050UVC-XPCA1	SMD	600 mA	80 mW	275 nm	120



UVC + UVA

Part No.	Package	Forward Current (IF)	Total Radiant Flux (mW)	Wavelength(nm)	Viewing Angle(°)
LT3535UVCA-K1PCG	SMD	40 mA / 150 mA	4.0 mW / 120 mW	280 nm / 410 nm	120



► Headquarters

光鼎電子股份有限公司
Para Light Electronics Co., Ltd.

新北市中和區建康路8號11樓
11F, No. 8, Jiankang Rd., Zhonghe Dist. New Taipei City, 23586 Taiwan
T+886-2-2225-3733
F+886-2-2225-4800
para@para.com.tw
www.para.com.tw

► Factory

連雲港光鼎電子有限公司
Para Light Lianyungang Electronics Co., Ltd.

中国江苏省连云港市灌南县经济开发区海路8号
No.8, Wei Hai Rd., Guannan Economics Deveopment Zone,
Lianyungang City, Jiangsu Province, 223500, China
T+86-518-8369-2888
F+86-518-8369-2899
para@para.com.tw

南京華鼎電子有限公司
Para Light Nanjing Electronics Co., Ltd.

中国江苏省南京市江宁区汤山街汤泉西路1号
No.1, Tanguan W. Rd., Tangshan Ave., Jianning Dist. Nanjing City,
Jiansu Province, 211131 China
T+86-25-8410-7685
F+86-25-8410-7684

仰光緬甸
Para Light Yangon (Myanmar)

Shwe Lin Pan Industrial area, Yangon City, Myanmar

► America

美國光鼎分公司
Para Light Corp. USA

515 Spanish Lane, Suite # A&B, Walnut, CA 91789, USA
T+1 (877) 377-PARA / T+1 (909) 468-4866
sales@paralightusa.com
www.paralightusa.com

► India

印度分公司
PARA LIGHT INDIA PVT. LTD.

No.979, 9th Floor, Aggarwal Cyber Plaza-2,
Netaji Subhash Place, Pitampura, New Delhi- 110034, India
T+011-41086226
abhinav.jha@para.com.tw

► Greater China-Sales Team

North China : Beijing, Qingdao
East China : Shanghai, Ningbo, Suzhou, Nanjing, Hefei, Wuhan, Zhengzhou
South: Shenzhen, Xiamen, Jiangmen
Central : Chengdu

蘇州光鼎電子有限公司 East China
Para Light (SUZHOU) Electronics Co., Ltd.

苏州新区狮山路199号新地中心2104室
Room 2104, Xindi Center Building, No.199, Shishan Road
Suzhou City, Jiangsu Province, 215011 China
T+86-133-6527-0527
F+86-512-6809-7669
jeremy@para-lyg.com.cn

光鼎深圳實業有限公司 South China
Para Light (SHENZHEN) Electronics Co., Ltd.

中国深圳市龙华区龙观东路57号尚美时代大厦1310-1312室
Room 1310-1312, Shangmei Times Building, No.57,
Longguan East Road, Longhua Dist., Shenzhen City,
Guangdong Province, 518110 China
T+86-189-2747-1103
eddy@paralight.com.cn

青島光鼎電子有限公司
Para Light (QINGDAO) Electronics Co., Ltd.

山东省青岛市市北区山东路168号时代国际广场12楼1204室
Room 1204, 12th Floor, Times International Plaza,
No.168 Shandong Road, Shibei District, Qingdao City,
Shandong Province, 266000 China
T+0532-85692571 / 18626429477

光鼎北京辦事處 North China
Para Light (BEIJING) Sales Office

北京市海淀区请和中街橡树湾二期
Qinghe street, oak bay Phase II building, Haiding District,
Beijing City, 100000 China
T+186-2642-9477 / 181-0107-7619
tianjin@paralight.com.cn

光鼎成都辦事處 Central China
Para Light (CHENGDU) Sales Office

四川省成都市金牛区金沙路169号-现代城1幢10层1008室
Room 1008, 10th Floor, No. 169 Xiandaicheng Building 1, Jinsha Road,
Jinniu District, Chengdu city, Sichuan Province, 610031 China
T+86-18360655305
yangfeiting@para-lyg.com.cn